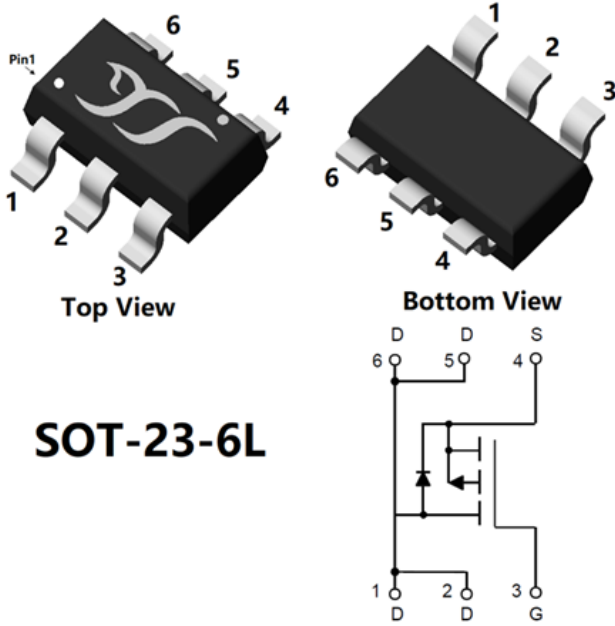


P-Channel Enhancement Mode Field Effect Transistor



SOT-23-6L

Product Summary

- V_{DS} -20V
- I_D -5.4A
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) 39mohm
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) 49mohm
- $R_{DS(ON)}$ (at $V_{GS}=-1.8V$) 63mohm
- 100% ∇V_{DS} Tested

General Description

- Trench Power LV MOSFET technology
- High Power and Current handling capability
- Low Gate Charge
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery protection
- Power management
- Load switch

■ Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-20	V
Gate-source Voltage		V_{GS}	10	V
Drain Current	$T_A=25$	I_D	-5.4	A
	$T_A=70$		-4.4	
Pulsed Drain Current ^A		I_{DM}	-22	A
Total Power Dissipation	$T_A=25$	P_D	1.2	W
	$T_A=70$		0.8	
Thermal Resistance Junction-to-Ambient ^B		$R_{\theta JA}$	104	/ W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJS2305A	F2	2305	3000	30000	120000	7" reel



YJS2305A

■ Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=10V, V_{DS}=0V$			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.62	-1.0	V

$V_{GS}=-4.5V,$

Static Drain-Source On-Resistance

$R_{DS(ON)}$



■ Typical Performance Characteristics

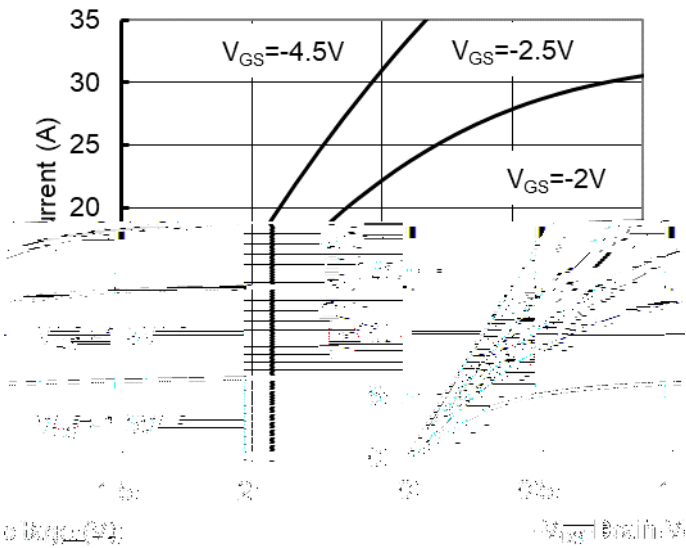


Figure1. Output Characteristics

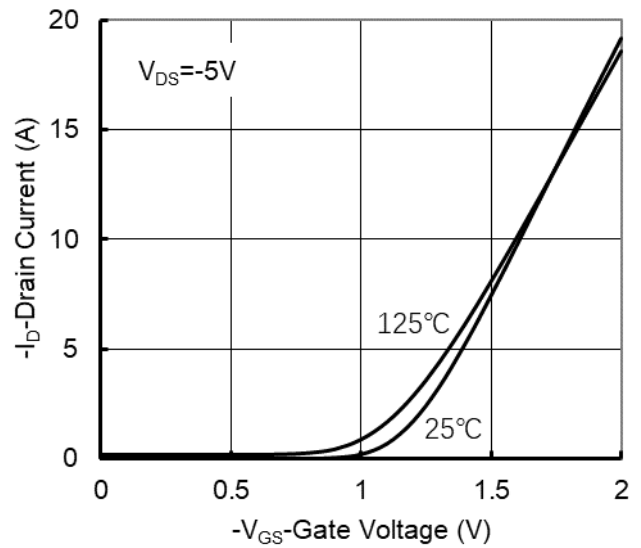


Figure2. Transfer Characteristics

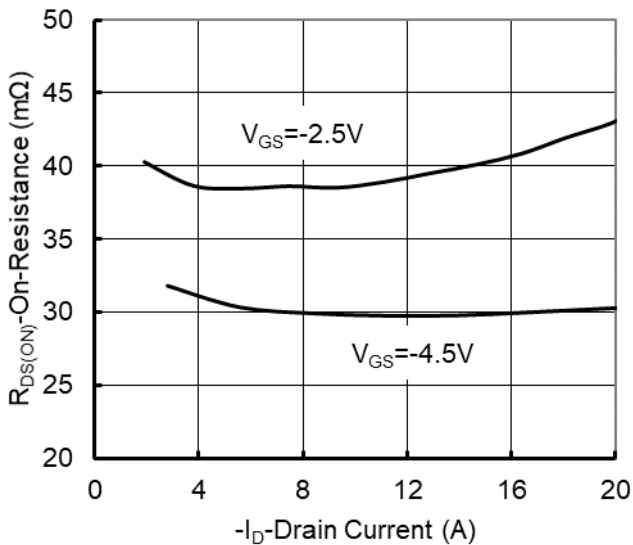


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

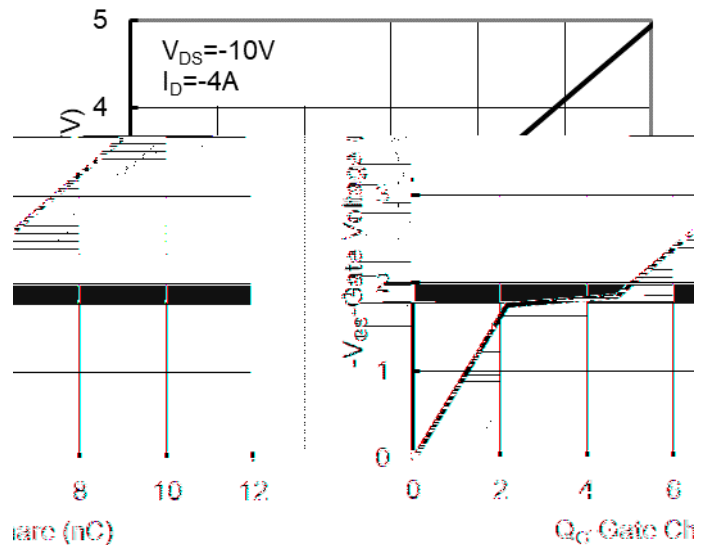


Figure 4: On-Resistance vs. Junction Temperature

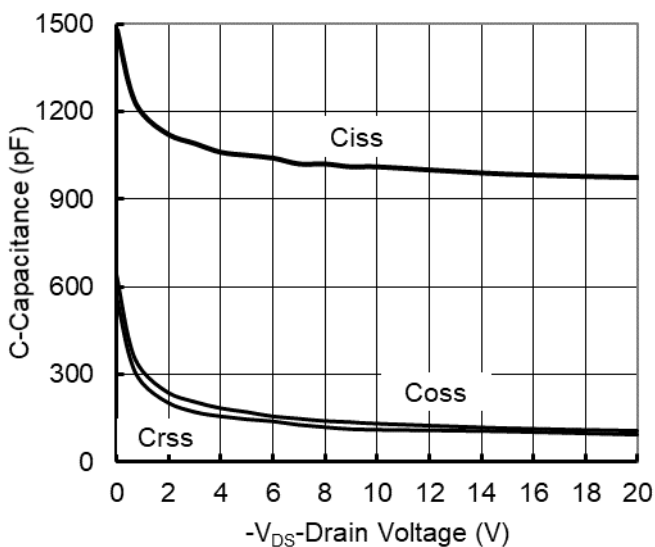


Figure5. Capacitance Characteristics

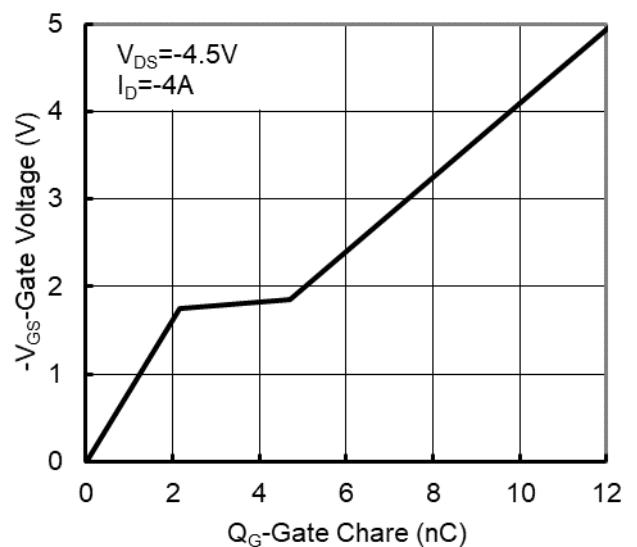


Figure6. Gate Charge

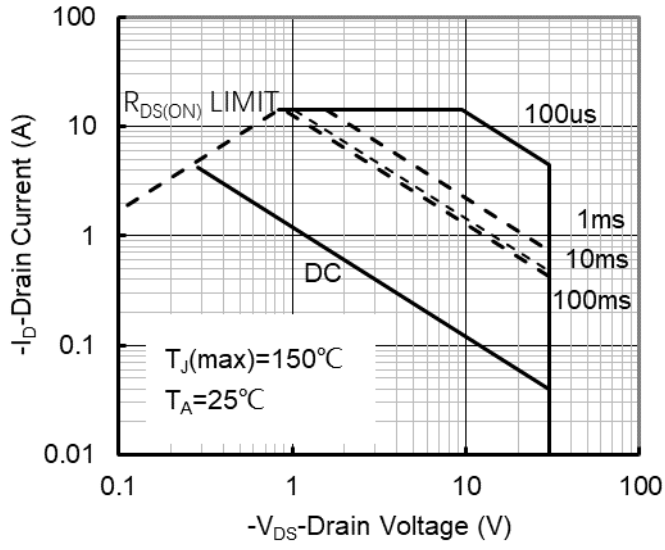
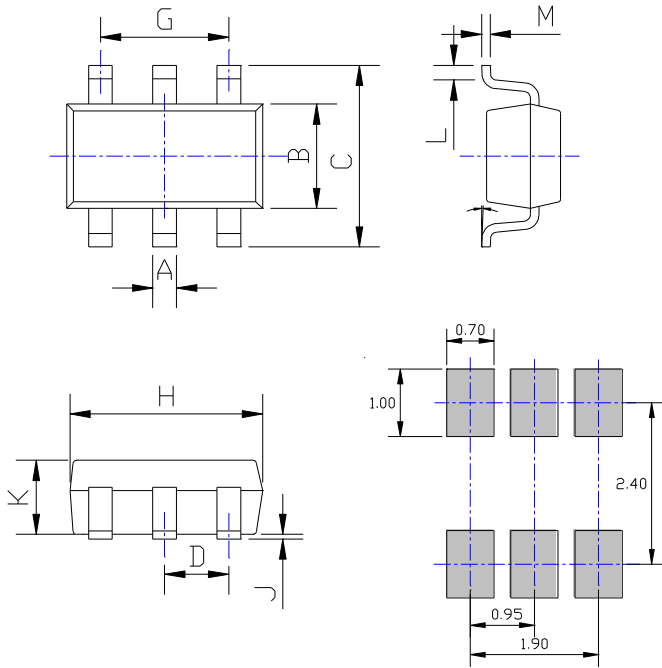


Figure7

■ SOT-23-6L Package Information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.012	0.020	0.300	0.500
B	0.059	0.067	1.500	1.700
C	0.104	0.116	2.650	2.950
D	0.037BSC		0.950BSC	
G	0.075BSC		1.900BSC	
H	0.111	0.119	2.820	3.020
J	0.000	0.004	0.000	0.100
K	0.041	0.045	1.050	1.150
L	0.012	0.024	0.300	0.600
M	0.004	0.008	0.100	0.200
	0°	8°	0°	8°

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.



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